



Integrated Device Technology, Inc.

HIGH-PERFORMANCE CMOS BUS INTERFACE REGISTERS

IDT54/74FCT821AT/BT/CT/DT
IDT54/74FCT823AT/BT/CT/DT
IDT54/74FCT825AT/BT/CT
IDT54/74FCT826AT/BT/CT

FEATURES:

- Fastest CMOS logic family available
- A, B, C and D speed grades with 4.2ns t_{PD}
- Available in DIP, SOIC, SSOP, CERPACK and LCC packages
- High-speed parallel registers with positive edge-triggered D-type flip-flops
- Buffered common Clock Enable (\overline{EN}) and asynchronous Clear input (CLR)
- IOL = 48mA (commercial) and 32mA (military)
- Clamp diodes on all inputs for ringing suppression
- CMOS power levels (1mW typ. static)
- True TTL input and output compatibility
 - VOH = 3.3V (typ.)
 - VOL = 0.3V (typ.)
- Substantially lower input current levels than AMD's bipolar Am29800 series (5 μ A max.)
- Product available in Radiation Tolerant and Radiation Enhanced versions
- Military product compliant to MIL-STD-883, Class B
- Meet or exceed JEDEC Standard 18 specifications

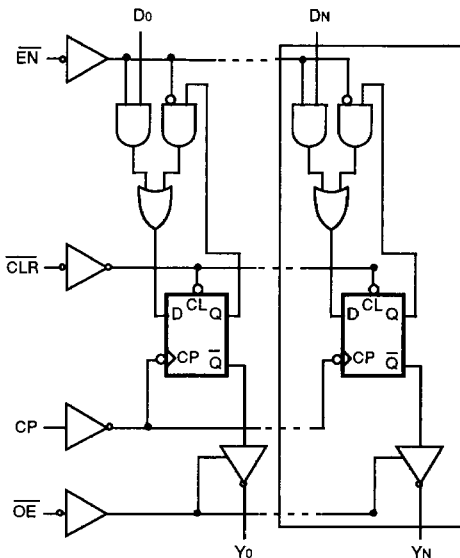
DESCRIPTION:

The IDT54/74FCT800 series is built using advanced CEMOS™, a dual metal CMOS technology.

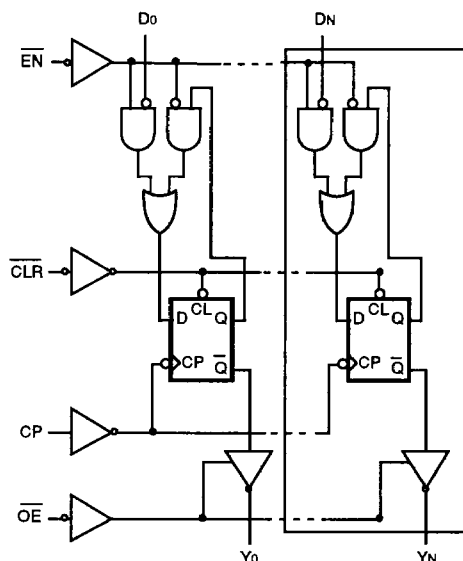
The IDT54/74FCT820 series bus interface registers are designed to eliminate the extra packages required to buffer existing registers and provide extra data width for wider address/data paths or buses carrying parity. The IDT54/74FCT821AT/BT/CT/DT are buffered, 10-bit wide versions of the popular '374 function. The IDT54/74FCT823AT/BT/CT/DT are 9-bit wide buffered registers with Clock Enable (EN) and Clear (CLR) – ideal for parity bus interfacing in high-performance microprogrammed systems. The IDT54/74FCT825AT/BT/CT and IDT54/74FCT826AT/BT/CT are 8-bit buffered registers with all the '823 controls plus multiple enables (OE1, OE2, OE3) to allow multiuser control of the interface, e.g., CS, DMA and RD/WR. They are ideal for use as an output port requiring high IOL/IOH.

All of the IDT54/74FCT800 high-performance interface family are designed for high-capacitance load drive capability, while providing low-capacitance bus loading at both inputs and outputs. All inputs have clamp diodes and all outputs are designed for low-capacitance bus loading in high-impedance state.

FUNCTIONAL BLOCK DIAGRAM IDT54/74FCT821/823/825T



IDT54/74FCT826T



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FAST is a trademark of National Semiconductor Co.

MILITARY AND COMMERCIAL TEMPERATURE RANGES

MAY 1992

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PRODUCT SELECTOR GUIDE

	Device		
	10-Bit	9-Bit	8-Bit
Non-inverting	FCT821AT/BT/CT/DT	FCT823AT/BT/CT/DT	FCT825AT/BT/CT
Inverting			FCT826AT/BT/CT

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PIN DESCRIPTION

Names	I/O	Description
D _i	I	The D flip-flop data inputs.
CLR	I	When the clear input is LOW and OE is LOW, the Q _i outputs are LOW. When the clear input is HIGH, data can be entered into the register.
CP	I	Clock Pulse for the Register; enters data into the register on the LOW-to-HIGH transition.
Y _i	O	The register 3-state outputs.
EN	I	Clock Enable. When the clock enable is LOW, data on the D _i input is transferred to the Q _i output on the LOW-to-HIGH clock transition. When the clock enable is HIGH, the Q _i outputs do not change state, regardless of the data or clock input transitions.
OE	I	Output Control. When the OE input is HIGH, the Y _i outputs are in the high-impedance state. When the OE input is LOW, the TRUE register data is present at the Y _i outputs.

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FUNCTION TABLE⁽¹⁾
IDT54/74FCT821/823/825T

Inputs					Internal/Outputs		Function
OE	CLR	EN	D _i	CP	Q _i	Y _i	
H	H	L	L	↑	L	Z	High Z
H	H	L	H	↑	H	Z	
H	L	X	X	X	L	Z	Clear
L	L	X	X	X	L	L	
H	H	H	X	X	NC	Z	Hold
L	H	H	X	X	NC	NC	
H	H	L	L	↑	L	Z	Load
H	H	L	H	↑	H	Z	
L	H	L	L	↑	L	L	
L	H	L	H	↑	H	H	

2567 tbl 03

NOTE:

- H = HIGH
L = LOW
X = Don't Care
NC = No Change
↑ = LOW-to-HIGH Transition
Z = High Impedance

FUNCTION TABLE⁽¹⁾
IDT54/74FCT826T

Inputs					Internal/Outputs		Function
OE	CLR	EN	D _i	CP	Q _i	Y _i	
H	H	L	L	↑	H	Z	High Z
H	H	L	H	↑	L	Z	
H	L	X	X	X	L	Z	Clear
L	L	X	X	X	L	L	
H	H	H	X	X	NC	Z	Hold
L	H	H	X	X	NC	NC	
H	H	L	L	↑	H	Z	Load
H	H	L	H	↑	L	Z	
L	H	L	L	↑	L	H	
L	H	L	H	↑	H	L	

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NOTE:

- H = HIGH
L = LOW
X = Don't Care
NC = No Change
↑ = LOW-to-HIGH Transition
Z = High Impedance

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ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Rating	Commercial	Military	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
VTERM ⁽³⁾	Terminal Voltage with Respect to GND	-0.5 to Vcc	-0.5 to Vcc	V
TA	Operating Temperature	0 to +70	-55 to +125	°C
TBIAS	Temperature Under Bias	-55 to +125	-65 to +135	°C
TSTG	Storage Temperature	-55 to +125	-65 to +150	°C
PT	Power Dissipation	0.5	0.5	W
IOUT	DC Output Current	120	120	mA

NOTES:

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- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability. No terminal voltage may exceed Vcc by +0.5V unless otherwise noted.
- Input and Vcc terminals only.
- Outputs and I/O terminals only.

CAPACITANCE (TA = +25°C, f = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Typ.	Max.	Unit
CIN	Input Capacitance	VIN = 0V	6	10	pF
COUT	Output Capacitance	VOU = 0V	8	12	pF

NOTE:

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- This parameter is measured at characterization but not tested.

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified:

Commercial: TA = 0°C to +70°C, Vcc = 5.0V ± 5%; Military: TA = -55°C to +125°C, Vcc = 5.0V ± 10%

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Typ. ⁽²⁾	Max.	Unit
VIH	Input HIGH Level	Guaranteed Logic HIGH Level		2.0	—	—	V
VIL	Input LOW Level	Guaranteed Logic LOW Level		—	—	0.8	V
IiH	Input HIGH Current	Vcc = Max.	Vi = 2.7V	—	—	5	µA
IiL	Input LOW Current	Vcc = Max.	Vi = 0.5V	—	—	-5	µA
IOZH	High Impedance Output Current	Vcc = Max.	Vo = 2.7V	—	—	10	µA
IOZL			Vo = 0.5V	—	—	-10	µA
Ii	Input HIGH Current	Vcc = Max., Vi = Vcc (Max.)		—	—	20	µA
VIK	Clamp Diode Voltage	Vcc = Min., IN = -18mA		—	-0.7	-1.2	V
Ios	Short Circuit Current	Vcc = Max. ⁽³⁾ , Vo = GND		-60	-120	-225	mA
VOH	Output HIGH Voltage	Vcc = Min. VIN = VIH or VIL	IOH = -6mA MIL. IOH = -8mA COM'L.	2.4	3.3	—	V
			IOH = -12mA MIL. IOH = -15mA COM'L.	2.0	3.0	—	V
VOL	Output LOW Voltage	Vcc = Min. VIN = VIH or VIL	IOL = 32mA MIL. IOL = 48mA COM'L.	—	0.3	0.5	V
VH	Input Hysteresis	—		—	200	—	mV
ICC	Quiescent Power Supply Current	Vcc = Max. VIN = GND or VCC		—	0.2	1.5	mA

NOTES:

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- For conditions shown as Max. or Min., use appropriate value specified under Electrical Characteristics for the applicable device type.
- Typical values are at Vcc = 5.0V, +25°C ambient and maximum loading.
- Not more than one output should be shorted at one time. Duration of the short circuit test should not exceed one second.

POWER SUPPLY CHARACTERISTICS

Symbol	Parameter	Test Conditions ⁽¹⁾	Min.	Typ. ⁽²⁾	Max.	Unit	
ΔI_{CC}	Quiescent Power Supply Current TTL inputs HIGH	$V_{CC} = \text{Max.}$ $V_{IN} = 3.4V^{(3)}$	—	0.5	2.0	mA	
I_{CCD}	Dynamic Power Supply Current ⁽⁴⁾	$V_{CC} = \text{Max.}$ Outputs Open $\overline{OE} = \overline{EN} = \text{GND}$ One Input Toggling 50% Duty Cycle	$V_{IN} = V_{CC}$ $V_{IN} = \text{GND}$	—	0.15	0.25	mA/ MHz
I_C	Total Power Supply Current ⁽⁶⁾	$V_{CC} = \text{Max.}$ Outputs Open $f_{CP} = 10\text{MHz}$ 50% Duty Cycle $\overline{OE} = \overline{EN} = \text{GND}$ One Bit Toggling at $f_i = 5\text{MHz}$ 50% Duty Cycle	$V_{IN} = V_{CC}$ $V_{IN} = \text{GND}$	—	1.7	4.0	mA
		$V_{IN} = 3.4V$ $V_{IN} = \text{GND}$	—	2.2	6.0		
		$V_{CC} = \text{Max.}$ Outputs Open $f_{CP} = 10\text{MHz}$ 50% Duty Cycle $\overline{OE} = \overline{EN} = \text{GND}$ Eight Bits Toggling at $f_i = 2.5\text{MHz}$ 50% Duty Cycle	$V_{IN} = V_{CC}$ $V_{IN} = \text{GND}$	—	4.0	7.8 ⁽⁵⁾	
		$V_{IN} = 3.4V$ $V_{IN} = \text{GND}$	—	6.2	16.8 ⁽⁵⁾		

NOTES:

- For conditions shown as Max. or Min., use appropriate value specified under Electrical Characteristics for the applicable device type.
- Typical values are at $V_{CC} = 5.0V$, $+25^\circ\text{C}$ ambient.
- Per TTL driven input ($V_{IN} = 3.4V$); all other inputs at V_{CC} or GND .
- This parameter is not directly testable, but is derived for use in Total Power Supply Calculations.
- Values for these conditions are examples of the I_{CC} formula. These limits are guaranteed but not tested.
- $I_C = I_{\text{QUIESCENT}} + I_{\text{INPUTS}} + I_{\text{DYNAMIC}}$
 $I_C = I_{CC} + \Delta I_{CC} D_{HNT} + I_{CCD} (f_{CP}/2 + f_i N_i)$
 $I_{CC} = \text{Quiescent Current}$
 $\Delta I_{CC} = \text{Power Supply Current for a TTL High Input } (V_{IN} = 3.4V)$
 $D_H = \text{Duty Cycle for TTL Inputs High}$
 $N_T = \text{Number of TTL Inputs at } D_H$
 $I_{CCD} = \text{Dynamic Current Caused by an Input Transition Pair (HLH or LHL)}$
 $f_{CP} = \text{Clock Frequency for Register Devices (Zero for Non-Register Devices)}$
 $f_i = \text{Input Frequency}$
 $N_i = \text{Number of Inputs at } f_i$
 All currents are in milliamps and all frequencies are in megahertz.

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SWITCHING CHARACTERISTICS OVER OPERATING RANGE

Symbol	Parameter	Condition ⁽¹⁾	FCT821AT-826AT				FCT821BT-826BT				Unit
			Com'l.		Mil.		Com'l.		Mil.		
			Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	
tPLH tPHL	Propagation Delay CP to Y _i (\overline{OE} = LOW)	CL = 50pF RL = 500Ω	1.5	10.0	1.5	11.5	1.5	7.5	1.5	8.5	ns
		CL = 300pF ⁽⁴⁾ RL = 500Ω	1.5	20.0	1.5	20.0	1.5	15.0	1.5	16.0	
tSU	Set-up Time HIGH or LOW DI to CP	CL = 50pF RL = 500Ω	4.0	—	4.0	—	3.0	—	3.0	—	ns
tH	Hold Time HIGH or LOW DI to CP		2.0	—	2.0	—	1.5	—	1.5	—	ns
tSU	Set-up Time HIGH or LOW \overline{EN} to CP		4.0	—	4.0	—	3.0	—	3.0	—	ns
tH	Hold Time HIGH or LOW \overline{EN} to CP		2.0	—	2.0	—	0	—	0	—	ns
tPHL	Propagation Delay, \overline{CLR} to Y _i		1.5	14.0	1.5	15.0	1.5	9.0	1.5	9.5	ns
tREM	Recovery Time \overline{CLR} to CP		6.0	—	7.0	—	6.0	—	6.0	—	ns
tW	Clock Pulse Width HIGH or LOW		7.0	—	7.0	—	6.0	—	6.0	—	ns
tW	CLR Pulse Width LOW		6.0	—	7.0	—	6.0	—	6.0	—	ns
tPZH tPZL	Output Enable Time \overline{OE} to Y _i		CL = 50pF RL = 500Ω	1.5	12.0	1.5	13.0	1.5	8.0	1.5	9.0
		CL = 300pF ⁽⁴⁾ RL = 500Ω	1.5	23.0	1.5	25.0	1.5	15.0	1.5	16.0	
tPHZ tPLZ	Output Disable Time \overline{OE} to Y _i	CL = 5pF ⁽⁴⁾ RL = 500Ω	1.5	7.0	1.5	8.0	1.5	6.5	1.5	7.0	ns
		CL = 50pF RL = 500Ω	1.5	8.0	1.5	9.0	1.5	7.5	1.5	8.0	

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NOTES:

1. See test circuit and waveforms.
2. Minimum limits are guaranteed but not tested on Propagation Delays.
3. This parameter is guaranteed but not tested.
4. This condition is guaranteed but not tested.

SWITCHING CHARACTERISTICS OVER OPERATING RANGE

Symbol	Parameter	Condition ⁽¹⁾	FCT821CT-826CT				FCT821DT		FCT823DT		Unit
			Com'l.		Mil.		Com'l.		Com'l.		
			Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	
tPLH tPHL	Propagation Delay CP to Y _i (\overline{OE} = LOW)	CL = 50pF RL = 500Ω	1.5	6.0	1.5	7.0	1.5	4.2	1.5	5.0	ns
		CL = 300pF ⁽⁴⁾ RL = 500Ω	1.5	12.5	1.5	13.5	1.5	8.0	1.5	8.5	
tSU	Set-up Time HIGH or LOW DI to CP	CL = 50pF RL = 500Ω	3.0	—	3.0	—	2.0	—	2.0	—	ns
tH	Hold Time HIGH or LOW DI to CP		1.5	—	1.5	—	1.0	—	1.0	—	ns
tSU	Set-up Time HIGH or LOW \overline{EN} to CP		3.0	—	3.0	—	3.0	—	3.0	—	ns
tH	Hold Time HIGH or LOW \overline{EN} to CP		0	—	0	—	0	—	0	—	ns
tPHL	Propagation Delay, \overline{CLR} to Y _i		1.5	8.0	1.5	8.5	1.5	5.0	1.5	5.0	ns
tREM	Recovery Time \overline{CLR} to CP		6.0	—	6.0	—	3.0	—	3.0	—	ns
tW	Clock Pulse Width HIGH or LOW ⁽³⁾		6.0	—	6.0	—	3.0	—	3.0	—	ns
tW	CLR Pulse Width LOW ⁽³⁾		6.0	—	6.0	—	3.0	—	3.0	—	ns
tPZH tPZL	Output Enable Time \overline{OE} to Y _i	CL = 50pF RL = 500Ω	1.5	7.0	1.5	8.0	1.5	4.8	1.5	4.8	ns
		CL = 300pF ⁽⁴⁾ RL = 500Ω	1.5	12.5	1.5	13.5	1.5	9.0	1.5	9.0	
tPHZ tPLZ	Output Disable Time \overline{OE} to Y _i	CL = 5pF ⁽⁴⁾ RL = 500Ω	1.5	6.0	1.5	6.0	1.5	4.0	1.5	4.0	ns
		CL = 50pF RL = 500Ω	1.5	6.5	1.5	6.5	1.5	4.0	1.5	4.0	

NOTES:

1. See test circuit and waveforms.
2. Minimum limits are guaranteed but not tested on Propagation Delays.
3. This parameter is guaranteed but not tested.
4. This condition is guaranteed but not tested.

2567 tbl 09

